(19) World Intellectual Property **Organization**

International Bureau





(43) International Publication Date 22 April 2004 (22.04.2004)

PCT

(10) International Publication Number WO 2004/034426 A3

H01L 29/10, (51) International Patent Classification⁷: 21/8234

(21) International Application Number:

PCT/US2003/030588

(22) International Filing Date:

23 September 2003 (23.09.2003)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

10/267,153

9 October 2002 (09.10.2002) US

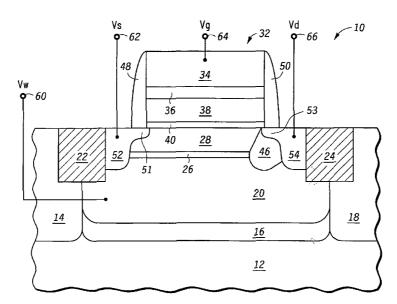
- (71) Applicant: MOTOROLA, INC. [US/US]; 1303 East Algonquin Road, Schaumburg, IL 60196 (US).
- (72) Inventors: CHINDALORE, Gowrishankar; 9101 Sautelle Lane, Austin, TX 78749 (US). INGERSOLL, Paul, A.; 6304 Old Harbor Lane, Austin, TX 78739 (US).

SWIFT, Craig, T.; 3613 Sawmill Drive, Austin, TX 78749 (US). HOEFLER, Alexander, B.; 2603 Rae Dell Avenue #4, Austin, TX 78704 (US).

- (74) Agents: WUAMETT, Jennifer, B. et al.; SPS PATENT OPERATION MANAGER - ON BEHALF OF MO-TOROLA, INC.; Corporate Law Department, Intellectual Property Section, 7700 West Parmer Lane, MD: TX32/PL02, Austin, TX 78729 (US).
- (81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (regional): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO,

[Continued on next page]

(54) Title: NON-VOLATILE MEMORY DEVICE AND METHOD FOR FORMING



(57) Abstract: In one embodiment, a semiconductor device (10) has a highly doped layer (26) having a first conductivity type uniformly implanted into a semiconductor substrate (20), where a channel region (28) is located between a top surface of the substrate (20) and the highly doped layer (26). In an alternate embodiment, a semiconductor device (70) has a counterdoped channel (86) and an anti-punch through region (74) below the channel. A gate stack (32) is formed over the substrate (20). A source (52) and drain (54, 53) having a second conductivity type are implanted into the substrate. The resulting non-volatile memory cell provides a low natural threshold voltage to minimize threshold voltage drift during a read cycle. In addition, a halo region (46), having the second conductivity type and implanted at an angle in the drain side, may be used to assist in hot carrier injection which allows a higher programming speed.

WO 2004/034426 A3



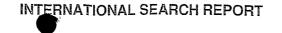
SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

Published:

- with international search report
- before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments
- (88) Date of publication of the international search report:

12 August 2004



Inter(nal Application No PCT/US 03/30588

a. classification of subject matter IPC 7 H01L29/10 H01 H01L21/8234 According to International Patent Classification (IPC) or to both national classification and IPC Minimum documentation searched (classification system followed by classification symbols) IPC 7 H01L Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched Electronic data base consulted during the international search (name of data base and, where practical, search terms used) EPO-Internal, PAJ C. DOCUMENTS CONSIDERED TO BE RELEVANT Citation of document, with indication, where appropriate, of the relevant passages Relevant to claim No. χ EP 0 513 923 A (PHILIPS NV) 1-5 19 November 1992 (1992-11-19) column 4, line 30 - column 9, line 14; figures 1-10 US 2002/024078 A1 (HORIUCHI MASATADA ET 1-4 AL) 28 February 2002 (2002-02-28) paragraphs [0013] - [0107]; figures 1-15 Α PATENT ABSTRACTS OF JAPAN 1,3,5 vol. 007, no. 226 (E-202), 7 October 1983 (1983-10-07) & JP 58 115863 A (MATSUSHITA DENKI SANGYO KK), 9 July 1983 (1983-07-09) abstract Further documents are listed in the continuation of box C. Patent family members are listed in annex. ° Special categories of cited documents: later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the "A" document defining the general state of the art which is not considered to be of particular relevance invention "E" earlier document but published on or after the international "X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to "L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified) involve an inventive step when the document is taken alone "Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such docu-"O" document referring to an oral disclosure, use, exhibition or ments, such combination being obvious to a person skilled in the art. document published prior to the international filing date but later than the priority date claimed "&" document member of the same patent family Date of the actual completion of the international search Date of mailing of the international search report 24 March 2004 02/07/2004 Name and mailing address of the ISA Authorized officer European Patent Office, P.B. 5818 Patentlaan 2 NL - 2280 HV Rijswijk Tel. (+31-70) 340-2040, Tx. 31 651 epo nl, Fax: (+31-70) 340-3016 Neumann, A

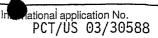
INTERNATIONAL SEARCH REPORT

ormation on patent family members

Internation No
PCT/US 03/30588

Patent document cited in search report	Publication date	Patent family member(s)	Publication date
EP 0513923	A 19-11-1992	US 5424567 A DE 69205060 D1 DE 69205060 T2 EP 0513923 A2 JP 5136427 A KR 258646 B1 US 5486480 A	13-06-1995 02-11-1995 15-05-1996 19-11-1992 01-06-1993 15-06-2000 23-01-1996
US 2002024078	41 28-02-2002	JP 2002076332 A TW 516234 B	15-03-2002 01-01-2003
JP 58115863	A 09-07-1983	NONE	

INTERNATIONAL SEARCH REPORT



Box I Observations where certain claims were found unsearchable (Continuation of item 1 of first sheet)				
This International Search Report has not been established in respect of certain claims under Article 17(2)(a) for the following reasons:				
Claims Nos.: because they relate to subject matter not required to be searched by this Authority, namely:				
2. Claims Nos.: because they relate to parts of the International Application that do not comply with the prescribed requirements to such an extent that no meaningful International Search can be carried out, specifically:				
3. Claims Nos.: because they are dependent claims and are not drafted in accordance with the second and third sentences of Rule 6.4(a).				
Box II Observations where unity of invention is lacking (Continuation of item 2 of first sheet)				
This International Searching Authority found multiple inventions in this international application, as follows:				
see additional sheet				
1. As all required additional search fees were timely paid by the applicant, this International Search Report covers all searchable claims.				
2. As all searchable claims could be searched without effort justifying an additional fee, this Authority did not invite payment of any additional fee.				
3. As only some of the required additional search fees were timely paid by the applicant, this International Search Report covers only those claims for which fees were paid, specifically claims Nos.:				
4. X No required additional search fees were timely paid by the applicant. Consequently, this International Search Report is restricted to the invention first mentioned in the claims; it is covered by claims Nos.:				
1-5	,			
Remark on Protest The additional search fees were accompanied by the applicant's protest.				
No protest accompanied the payment of additional search fees.	-			

FURTHER INFORMATION CONTINUED FROM PCT/ISA/ 210

This International Searching Authority found multiple (groups of) inventions in this international application, as follows:

1. claims: 1-5

Transistor with a halo implant in the drain and an anti-punch-through layer in the channel that contains dopants of a single conductivity type

2. claims: 6-10

Transistor with an anti-punch-through layer in the channel that contains dopants of two conductivity types